

Bruce W Wessels

List of Publications by Year in descending order

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docs citations

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Crystal Growth of the Perovskite Semiconductor CsPbBr ₃ : A New Material for High-Energy Radiation Detection. <i>Crystal Growth and Design</i> , 2013, 13, 2722-2727.	1.4	1,234
2	Strong Electron-Phonon Coupling and Self-Trapped Excitons in the Defect Halide Perovskites A ₃ M ₂ I ₉ (A = Cs, Rb; M = Bi, Sb). <i>Chemistry of Materials</i> , 2017, 29, 4129-4145.	3.2	509
3	High spectral resolution of gamma-rays at room temperature by perovskite CsPbBr ₃ single crystals. <i>Nature Communications</i> , 2018, 9, 1609.	5.8	381
4	Luminescence of heteroepitaxial zinc oxide. <i>Applied Physics Letters</i> , 1988, 52, 138-140. Excitonic emissions and above-band-gap luminescence in the single-crystal perovskite semiconductors	1.5	293
5	Excitonic emissions and above-band-gap luminescence in the single-crystal perovskite semiconductors		250
6	Behavior of 2.8- and 3.2-eV photoluminescence bands in Mg-doped GaN at different temperatures and excitation densities. <i>Physical Review B</i> , 1999, 59, 13176-13183.	1.1	222
7	CsPbBr ₃ perovskite detectors with 1.4% energy resolution for high-energy $\hat{\gamma}$ -rays. <i>Nature Photonics</i> , 2021, 15, 36-42.	15.6	210
8	Dimensional Reduction: A Design Tool for New Radiation Detection Materials. <i>Advanced Materials</i> , 2011, 23, 4163-4167.	11.1	185
9	Epitaxial growth of BaTiO ₃ thin films by organometallic chemical vapor deposition. <i>Applied Physics Letters</i> , 1992, 60, 41-43.	1.5	152
10	Optical properties of the deep Mn acceptor in GaN:Mn. <i>Applied Physics Letters</i> , 2002, 80, 1731-1733.	1.5	152
11	Ferroelectric Epitaxial Thin Films for Integrated Optics. <i>Annual Review of Materials Research</i> , 2007, 37, 659-679.	4.3	149
12	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via $\hat{\alpha}$ -Dip-Pen Nanolithography and Wet Chemical Etching. <i>Advanced Materials</i> , 2000, 12, 1600-1603.	11.1	129
13	Thin-film channel waveguide electro-optic modulator in epitaxial BaTiO ₃ . <i>Applied Physics Letters</i> , 1997, 71, 1783-1785.	1.5	127
14	Dielectric properties of epitaxial BaTiO ₃ thin films. <i>Applied Physics Letters</i> , 1998, 73, 2248-2250.	1.5	119
15	From 0D Cs ₃ Bi ₂ I ₉ to 2D Cs ₃ Bi ₂ I ₆ Cl ₃ : Dimensional Expansion Induces a Direct Band Gap but Enhances Electron-Phonon Coupling. <i>Chemistry of Materials</i> , 2019, 31, 2644-2650.	3.2	111
16	Investigation of the formation of the 2.8 eV luminescence band in p-type GaN:Mg. <i>Applied Physics Letters</i> , 2000, 76, 3011-3013.	1.5	108
17	Thallium Chalcogenides for X-ray and $\hat{\gamma}$ -ray Detection. <i>Journal of the American Chemical Society</i> , 2011, 133, 10030-10033.	6.6	105
18	Photoluminescence band near 2.9 eV in undoped GaN epitaxial layers. <i>Journal of Applied Physics</i> , 2000, 87, 3351-3354.	1.1	103

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19	Resolving the Energy of $\hat{\Gamma}^3$ -Ray Photons with MAPbI ₃ Single Crystals. ACS Photonics, 2018, 5, 4132-4138.	3.2	100
20	Electrical properties of p-type GaN:Mg codoped with oxygen. Applied Physics Letters, 2001, 78, 222-224.	1.5	88
21	$\hat{\Gamma}^{\pm}$ -Particle Detection and Charge Transport Characteristics in the A ₃ M ₂ I ₉ Defect Perovskites (A = Cs, Rb; M = Bi, Sb). ACS Photonics, 2018, 5, 3748-3762.	3.2	88
22	Thallium Chalcogenide-Based Wide-Band-Gap Semiconductors: TlGaSe ₂ for Radiation Detectors. Chemistry of Materials, 2011, 23, 3120-3128.	3.2	87
23	Electrooptic modulation up to 40 GHz in a barium titanate thin film waveguide modulator. Optics Express, 2004, 12, 5962.	1.7	85
24	Perovskite CsPbBr ₃ single crystal detector for alpha-particle spectroscopy. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2019, 922, 217-221.	0.7	83
25	Cs ₂ M ^{II} M ^{IV} ₃ Q ₈ (Q = S, Se, Te): An Extensive Family of Layered Semiconductors with Diverse Band Gaps. Chemistry of Materials, 2013, 25, 3344-3356.	3.2	75
26	Thin film channel waveguides fabricated in metalorganic chemical vapor deposition grown BaTiO ₃ on MgO. Applied Physics Letters, 1996, 69, 2968-2970.	1.5	74
27	Metal-Organic Chemical Vapor Deposition of Ferroelectric Oxide Thin Films for Electronic and Optical Applications. Annual Review of Materials Research, 1995, 25, 525-546.	5.5	68
28	Thermal quenching of Er ³⁺ -related luminescence in In _{1-x} GaxP. Applied Physics Letters, 1992, 60, 2657-2659.	1.5	67
29	InAs/InP strained single quantum wells grown by atmospheric pressure organometallic vapor phase epitaxy. Applied Physics Letters, 1990, 57, 1998-2000.	1.5	66
30	Low-voltage, polarization-insensitive, electro-optic modulator based on a polydomain barium titanate thin film. Applied Physics Letters, 2004, 85, 4615-4617.	1.5	66
31	Organometallic chemical vapor deposition of strontium titanate. Journal of Applied Physics, 1990, 67, 3858-3861.	1.1	65
32	Demonstration of Energy-Resolved $\hat{\Gamma}^3$ -Ray Detection at Room Temperature by the CsPbCl ₃ Perovskite Semiconductor. Journal of the American Chemical Society, 2021, 143, 2068-2077.	6.6	62
33	Carbon- ¹³ C hydrogen complexes in vapor phase epitaxial GaN. Applied Physics Letters, 1997, 70, 357-359.	1.5	61
34	Direct thermal neutron detection by the 2D semiconductor 6LiInP ₂ Se ₆ . Nature, 2020, 577, 346-349.	18.7	59
35	Electrical transport properties of epitaxial BaTiO ₃ thin films. Journal of Applied Physics, 1996, 80, 969-977.	1.1	56
36	CsHgInS ₃ : a New Quaternary Semiconductor for $\hat{\Gamma}^3$ -ray Detection. Chemistry of Materials, 2012, 24, 4434-4441.	3.2	56

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37	Photoconductivity in the Chalcogenide Semiconductor, SbSeI: a New Candidate for Hard Radiation Detection. Inorganic Chemistry, 2013, 52, 7045-7050.	1.9	55
38	Magnetotransport properties of InMnSb magnetic semiconductor thin films. Physical Review B, 2010, 82, .	1.1	54
39	Photoluminescence properties of Er ³⁺ -doped BaTiO ₃ thin films. Applied Physics Letters, 1994, 65, 25-27.	1.5	51
40	Nonlinear optical properties of textured strontium barium niobate thin films prepared by metalorganic chemical vapor deposition. Applied Physics Letters, 1995, 66, 1726-1728.	1.5	51
41	CsCdInQ ₃ (Q = Se, Te): New Photoconductive Compounds As Potential Materials for Hard Radiation Detection. Chemistry of Materials, 2013, 25, 2089-2099.	3.2	50
42	Growth and characterization of OMVPE grown (In,Mn)As diluted magnetic semiconductor. Journal of Electronic Materials, 2001, 30, 1408-1411.	1.0	48
43	Relative dielectric constant of epitaxial BaTiO ₃ thin films in the GHz frequency range. Applied Physics Letters, 2003, 83, 5274-5276.	1.5	46
44	Local structure around Mn atoms in room-temperature ferromagnetic (In,Mn)As thin films probed by extended x-ray absorption fine structure. Applied Physics Letters, 2004, 84, 481-483.	1.5	45
45	Photoconductivity in Tl ₆ Si ₄ : A Novel Semiconductor for Hard Radiation Detection. Chemistry of Materials, 2013, 25, 2868-2877.	3.2	45
46	Defect Antiperovskite Compounds Hg ₃ Q ₂ I ₂ (Q = S, Se, and Te) for Room-Temperature Hard Radiation Detection. Journal of the American Chemical Society, 2017, 139, 7939-7951.	6.6	45
47	Photoluminescent properties of Er-doped In ^x GaxP prepared by metalorganic vapor phase epitaxy. Applied Physics Letters, 1991, 59, 2317-2319.	1.5	44
48	Epitaxial potassium niobate thin films prepared by metalorganic chemical vapor deposition. Applied Physics Letters, 1995, 67, 365-367.	1.5	44
49	Crystal Growth and Characterization of the X-ray and γ -ray Detector Material Cs ₂ Hg ₆ S ₇ . Crystal Growth and Design, 2012, 12, 3250-3256.	1.4	42
50	Optical properties of InAs/InP strained single quantum wells grown by organometallic vapor-phase epitaxy. Journal of Applied Physics, 1991, 70, 405-408.	1.1	41
51	Interfacial structure and chemistry of epitaxial CoFe ₂ O ₄ thin films on SrTiO ₃ and MgO substrates. Applied Physics Letters, 2008, 93, 181901.	1.5	41
52	BaTiO ₃ thin-film waveguide modulator with a low voltage-length product at near-infrared wavelengths of 098 and 155 μ m. Optics Letters, 2005, 30, 254.	1.7	40
53	Epitaxial growth and strain relaxation of BaTiO ₃ thin films on SrTiO ₃ buffered (001) Si by molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2007, 25, 1053.	1.3	40
54	Microstructure of epitaxial potassium niobate thin films prepared by metalorganic chemical vapor deposition. Applied Physics Letters, 1996, 68, 761-763.	1.5	39

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55	Magnetoamplification in a Bipolar Magnetic Junction Transistor. <i>Physical Review Letters</i> , 2010, 105, 117202.	2.9	39
56	Cascaded spintronic logic with low-dimensional carbon. <i>Nature Communications</i> , 2017, 8, 15635.	5.8	39
57	Negative magnetoresistance in (In,Mn)As semiconductors. <i>Physical Review B</i> , 2004, 70, .	1.1	35
58	Crystal Growth of $\text{Te}_{1-x}\text{Cd}_x$: A Wide Band Gap Semiconductor for Hard Radiation Detection. <i>Crystal Growth and Design</i> , 2014, 14, 2401-2410.	1.4	35
59	Preparation of high- T_c superconducting $\text{Bi}_{1-x}\text{Sr}_x\text{Ca}_y\text{Cu}_z\text{O}$ films by organometallic chemical vapor deposition using second-generation fluorocarbon-based precursors. <i>Journal of Applied Physics</i> , 1991, 69, 2743-2745.	1.1	33
60	Hard Radiation Detection from the Selenophosphate $\text{Pb}_2\text{P}_2\text{Se}_6$. <i>Advanced Functional Materials</i> , 2015, 25, 4874-4881.	7.8	33
61	TeSn_2I_5 , a Robust Halide Antiperovskite Semiconductor for $\hat{\gamma}$ -Ray Detection at Room Temperature. <i>ACS Photonics</i> , 2017, 4, 1805-1813.	3.2	33
62	High-conductivity heteroepitaxial ZnSe films. <i>Applied Physics Letters</i> , 1980, 37, 955-957.	1.5	32
63	Growth kinetics of ZnO prepared by organometallic chemical vapor deposition. <i>Journal of Materials Research</i> , 1988, 3, 740-744.	1.2	32
64	MOCVD of Epitaxial BaTiO_3 Films Using a Liquid Barium Precursor. <i>Chemical Vapor Deposition</i> , 2000, 6, 175-177.	1.4	32
65	Optical properties of Mn^{4+} ions in GaN:Mn codoped with Mg acceptors. <i>Applied Physics Letters</i> , 2004, 84, 5320-5322.	1.5	32
66	Strain-driven spin reorientation in magnetite/barium titanate heterostructures. <i>Applied Physics Letters</i> , 2010, 96, .	1.5	32
67	Ferromagnetic InMnSb multi-phase films study by aberration-corrected (scanning) transmission electron microscopy. <i>Journal of Applied Physics</i> , 2012, 111, 07C311.	1.1	32
68	Deep level defects in heteroepitaxial zinc selenide. <i>Journal of Applied Physics</i> , 1982, 53, 3076-3084.	1.1	31
69	Monolayer abruptness in highly strained $\text{InAs}_x\text{P}_{1-x}/\text{InP}$ quantum well interfaces. <i>Applied Physics Letters</i> , 1989, 54, 1142-1144.	1.5	31
70	Luminescence quenching in Er-doped BaTiO_3 thin films. <i>Applied Physics Letters</i> , 1998, 73, 1625-1627.	1.5	30
71	Ferromagnetism in (In,Mn)As diluted magnetic semiconductor thin films grown by metalorganic vapor phase epitaxy. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2002, 20, 1582.	1.6	30
72	Blue emission band in compensated GaN:Mg codoped with Si. <i>Physical Review B</i> , 2003, 68, .	1.1	30

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73	Optical investigation of electronic states of Mn ⁴⁺ ions in p-type GaN. Applied Physics Letters, 2005, 86, 042505.	1.5	30
74	Ferromagnetic semiconductors and the role of disorder. New Journal of Physics, 2008, 10, 055008.	1.2	30
75	Morphological stability of strained-layer semiconductors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 1056.	1.6	29
76	Giant magnetoresistance of magnetic semiconductor heterojunctions. Physical Review B, 2009, 79, .	1.1	29
77	Photonic Crystal Waveguide Electro-Optic Modulator With a Wide Bandwidth. Journal of Lightwave Technology, 2013, 31, 1601-1607.	2.7	29
78	Epitaxial growth of SrTiO ₃ thin films by metalorganic chemical vapor deposition. Applied Physics Letters, 1995, 66, 3298-3300.	1.5	28
79	Epitaxial growth and strain relaxation of MgO thin films on Si grown by molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2006, 24, 2586.	1.3	28
80	A Spin-Diode Logic Family. IEEE Nanotechnology Magazine, 2012, 11, 1026-1032.	1.1	28
81	Scanning tunneling optical spectroscopy of semiconductors. Applied Physics Letters, 1991, 58, 1295-1296.	1.5	27
82	Electroluminescence from Er-doped GaP. Applied Physics Letters, 1994, 65, 584-586.	1.5	26
83	High-field magnetoresistance in p-(In,Mn)As/n-InAs heterojunctions. Applied Physics Letters, 2006, 88, 072105.	1.5	26
84	$\chi^{(2)}$ Modulator With 40-GHz Modulation Utilizing BaTiO ₃ Photonic Crystal Waveguides. IEEE Journal of Quantum Electronics, 2017, 53, 1-10.	1.0	26
85	Dynamic Disorder, Band Gap Widening, and Persistent Near-IR Photoluminescence up to At Least 523 K in ASn ₃ Perovskites (A = Cs, CH ₃ NH ₃) Tj ETQq _{1.1} 0.784314 rgB ₂₆ 26353-26361.	1.5	26
86	Thermal quenching properties of Er-doped GaP. Applied Physics Letters, 1994, 64, 1537-1539.	1.5	25
87	Dynamic response of the electro-optic effect in epitaxial KNbO ₃ . Applied Physics Letters, 1999, 75, 2707-2709.	1.5	25
88	High-temperature ferromagnetism in epitaxial (In,Mn)Sb films. Physical Review B, 2010, 81, .	1.1	25
89	Fast time-resolved x-ray diffraction in BaTiO ₃ films subjected to a strong high-frequency electric field. Applied Physics Letters, 2002, 80, 3159-3161.	1.5	24
90	Electronic and optical properties of Fe-doped InP prepared by organometallic vapor-phase epitaxy. Journal of Applied Physics, 1986, 60, 4342-4344.	1.1	23

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91	Strained-layer InSb/GaSb quantum wells grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 1993, 63, 628-630.	1.5	23
92	Dynamic response of the dielectric and electro-optic properties of epitaxial ferroelectric thin films. Physical Review B, 2002, 65, .	1.1	23
93	Characterization of Mn-doped InAsP \tilde{x} grown by organometallic vapor phase epitaxy. Applied Physics Letters, 1988, 52, 1155-1157.	1.5	22
94	Dielectric properties of epitaxial KNbO ₃ ferroelectric thin films. Journal of Materials Research, 2002, 17, 275-278.	1.2	22
95	Perovskites with a Twist: Strong In ¹⁺ Off-Centering in the Mixed-Valent CsInX ₃ (X = Cl, Br). Chemistry of Materials, 2019, 31, 9554-9566.	3.2	22
96	Structure of organometallic chemical vapor deposited BaTiO ₃ thin films on LaAlO ₃ . Journal of Electronic Materials, 1993, 22, 701-703.	1.0	21
97	On the microstructure, chemistry, and dielectric function of BaTiO ₃ MOCVD thin films. Journal of Materials Research, 1994, 9, 426-430.	1.2	21
98	Diffuse Phase Transition in Epitaxial BaTiO ₃ Thin Films. Journal of Materials Research, 2002, 17, 669-674.	1.2	21
99	Spin-dependent magnetotransport in a p-InMnSb/n-InSb magnetic semiconductor heterojunction. Applied Physics Letters, 2011, 98, 193506.	1.5	20
100	Detection of traps in high conductivity ZnSe by optical transient capacitance spectroscopy. Journal of Applied Physics, 1983, 54, 4205-4208.	1.1	19
101	Epitaxial Niobate Thin Films and Their Nonlinear Optical Properties. Materials Research Society Symposia Proceedings, 1995, 401, 211.	0.1	19
102	Thallous chalcogenide (Tl ₆ I ₄ Se) for radiation detection at X-ray and $\hat{\nu}$ -ray energies. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2011, 659, 333-335.	0.7	19
103	Cu ₂ I ₂ Se ₆ : A Metal-Inorganic Framework Wide-Bandgap Semiconductor for Photon Detection at Room Temperature. Journal of the American Chemical Society, 2018, 140, 1894-1899.	6.6	19
104	Heteroepitaxial growth of high mobility InAsP from the vapor phase. Applied Physics Letters, 1984, 44, 766-768.	1.5	18
105	Polarization reversal and backswitching dynamics in epitaxial BaTiO ₃ thin films. Journal of Applied Physics, 2009, 106, 054113.	1.1	18
106	Magnetism and Mn Clustering in (In,Mn)Sb Magnetic Semiconductors. ACS Applied Materials & Interfaces, 2015, 7, 24159-24167.	4.0	18
107	Electron mobility and carrier concentration of heteroepitaxial zinc selenide. Journal of Applied Physics, 1982, 53, 532-535.	1.1	17
108	Deep-level properties of Mn in InP. Journal of Applied Physics, 1990, 67, 6882-6885.	1.1	17

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109	Scanning tunneling optical spectroscopy of semiconductor quantum well structures. Applied Physics Letters, 1991, 58, 2538-2539.	1.5	17
110	Temperature dependent photoluminescent properties of InAs _x P _{1-x} /InP strained-layer quantum wells. Journal of Applied Physics, 1992, 72, 3041-3045.	1.1	16
111	Local environment of ferromagnetically ordered Mn in epitaxial InMnAs. Applied Physics Letters, 2005, 86, 072505.	1.5	16
112	Highly efficient broadband second harmonic generation using polydomain epitaxial barium titanate thin film waveguides. Applied Physics Letters, 2008, 92, .	1.5	16
113	Photoluminescence fatigue and inhomogeneous line broadening in semi-insulating Tl ₆ Se ₄ single crystals. Semiconductor Science and Technology, 2016, 31, 065009.	1.0	16
114	An Unusual Crystal Growth Method of the Chalcogenide Semiconductor, Hg ₃ S ₂ Cl ₂ : A New Candidate for Hard Radiation Detection. Crystal Growth and Design, 2016, 16, 2678-2684.	1.4	16
115	Inorganic Halide Perovskitoid TlPb ₃ for Ionizing Radiation Detection. Advanced Functional Materials, 2021, 31, 2006635.	7.8	16
116	Phase stability of epitaxial KTa _x Nb _{1-x} O ₃ thin films deposited by metalorganic chemical vapor deposition. Journal of Materials Research, 2003, 18, 106-110.	1.2	16
117	Electron-beam-enhanced oxidation processes in II-VI compound semiconductors observed by high-resolution electron microscopy. Journal of Applied Physics, 1990, 67, 1535-1541.	1.1	15
118	Hydrogen complexes in epitaxial BaTiO ₃ thin films. Applied Physics Letters, 1997, 71, 327-329.	1.5	15
119	Low temperature deposition of epitaxial BaTiO ₃ films in a rotating disk vertical MOCVD reactor. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1674.	1.6	15
120	Cyclotron resonance in ferromagnetic InMnAs and InMnSb. Physical Review B, 2013, 88, .	1.1	15
121	Charge Transport and Observation of Persistent Photoconductivity in Tl ₆ Se ₄ Single Crystals. Journal of Physical Chemistry Letters, 2017, 8, 1538-1544.	2.1	15
122	Role of Stoichiometry in the Growth of Large Pb ₂ P ₂ Se ₆ Crystals for Nuclear Radiation Detection. ACS Photonics, 2018, 5, 566-573.	3.2	15
123	Yb-doped InP grown by metalorganic vapor phase epitaxy using a beta-diketonate precursor. Applied Physics Letters, 1990, 56, 566-568.	1.5	14
124	Defect structure of strontium titanate thin films. Journal of Applied Physics, 1993, 74, 3927-3931.	1.1	14
125	Photoluminescent properties of Er-doped GaP deposited on Si. Applied Physics Letters, 1995, 67, 518-520.	1.5	14
126	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 301-307.	1.0	14

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127	Dependence of magnetic circular dichroism on doping and temperature in $\text{In}_{1-x}\text{Mn}_x\text{As}$ epitaxial films. Physical Review B, 2007, 76, .	1.1	14
128	Investigation of defect levels in Cs ₂ Hg ₆ S ₇ single crystals by photoconductivity and photoluminescence spectroscopies. Journal of Applied Physics, 2012, 112, 063702.	1.1	14
129	Carrier recombination mechanism in CsPbBr_3 revealed by time-resolved photoluminescence spectroscopy. Physical Review B, 2019, 100, .	1.1	14
130	Nitrogen related defect centers in zinc selenide. Journal of Applied Physics, 1984, 55, 1614-1616.	1.1	13
131	Nitrogen Doping of ZnO Prepared by Organometallic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1989, 152, 215.	0.1	13
132	Comparative optical studies of p-type and unintentionally doped GaN: The influence of annealing. Applied Physics Letters, 2001, 78, 58-60.	1.5	13
133	Three Dimensional Domain Structure in Epitaxial Barium Titanate Thin Films. Journal of Electroceramics, 2004, 13, 89-93.	0.8	13
134	Investigation of composition fluctuations in GaN:Mg using optical transmission spectroscopy, near-field scanning optical microscopy, and scanning Kelvin probe microscopy. Journal of Applied Physics, 2005, 98, 023513.	1.1	13
135	Time-resolved differential transmission in MOVPE-grown ferromagnetic InMnAs. Physical Review B, 2012, 85, .	1.1	13
136	Refined Synthesis and Crystal Growth of $\text{Pb}_2\text{P}_2\text{Se}_6$ for Hard Radiation Detectors. Crystal Growth and Design, 2016, 16, 5100-5109.	1.4	12
137	Electronic and photoluminescent properties of InP prepared by flow modulation epitaxy. Journal of Applied Physics, 1992, 71, 281-288.	1.1	11
138	Formation of native defects in the $\hat{\gamma}$ -ray detector material Cs ₂ Hg ₆ S ₇ . Applied Physics Letters, 2012, 101, .	1.5	11
139	Investigation of Semi-Insulating $\text{Cs}_2\text{Hg}_6\text{S}_7$ and $\text{Cs}_2\text{Hg}_6\text{Cd}_x\text{S}_7$ Alloy for Hard Radiation Detection. Crystal Growth and Design, 2014, 14, 5949-5956.	1.4	11
140	Emitter-Coupled Spin-Transistor Logic: Cascaded Spintronic Computing Beyond 10 GHz. IEEE Journal on Emerging and Selected Topics in Circuits and Systems, 2015, 5, 17-27.	2.7	11
141	TiSbS_2 : a Semiconductor for Hard Radiation Detection. ACS Photonics, 2017, 4, 2891-2898.	3.2	11
142	Photoluminescence spectroscopy of excitonic emission in CsPbCl ₃ perovskite single crystals. Journal of Luminescence, 2022, 243, 118661.	1.5	11
143	High conductivity zinc sulfoselenide thin films. Applied Physics Letters, 1982, 41, 165-167.	1.5	10
144	Electronic and optical properties of deep levels in iron-doped InAsP alloys. Journal of Applied Physics, 1988, 64, 6770-6774.	1.1	10

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145	Photoconductive properties of the Er-doped InP. Applied Physics Letters, 1994, 64, 466-468.	1.5	10
146	Electroluminescence from forward-biased Er-doped GaP p-n junctions at room temperature. Applied Physics Letters, 1996, 68, 1126-1128.	1.5	10
147	Evidence of room temperature sp-d exchange in InMnAs epitaxial films. Applied Physics Letters, 2006, 89, 102505.	1.5	10
148	Observation of enhanced photoluminescence in erbium-doped semiconductor microdisk resonator. Applied Physics Letters, 1995, 66, 2843-2845.	1.5	9
149	Dielectric properties of plasma-spray-deposited BaTiO ₃ and Ba _{0.68} Sr _{0.32} TiO ₃ thick films. Journal of Materials Research, 2003, 18, 1227-1231.	1.2	9
150	Thin Film Ferroelectrics for Guided Wave Devices. Journal of Electroceramics, 2004, 13, 135-138.	0.8	9
151	Local electronic and magnetic structure of mixed ferrite multilayer materials. Physical Review B, 2010, 81, .	1.1	9
152	Using the infrared magnetorefractive effect to compare the magnetoresistance in (100) and (111) oriented Fe ₃ O ₄ films. Journal of Applied Physics, 2010, 107, 09B102.	1.1	9
153	An Effective Purification Process for the Nuclear Radiation Detector Tl ₆ Se ₄ . Crystal Growth and Design, 2018, 18, 3484-3493.	1.4	9
154	Symmetry properties of Er ³⁺ -related centers in In _{1-x} Ga _x P with low alloy compositions. Applied Physics Letters, 1992, 61, 2461-2463.	1.5	8
155	Epitaxial Ferroelectric BaTiO ₃ Thin Films for Microphotonic Applications. Materials Research Society Symposia Proceedings, 2000, 637, E1.9.1.	0.1	8
156	Dynamic response of polydomain ferroelectric barium titanate epitaxial thin films and its field dependence. Journal of Applied Physics, 2008, 104, 064115.	1.1	8
157	Mercury and antimony chalcogenide semiconductors as new candidates for radiation detection applications at room temperature. Proceedings of SPIE, 2012, , .	0.8	8
158	Emitter-coupled spin-transistor logic. Journal of Parallel and Distributed Computing, 2014, 74, 2461-2469.	2.7	8
159	High-field magnetic circular dichroism in ferromagnetic InMnSb and InMnAs: Spin-orbit-split hole bands and g factors. Physical Review B, 2015, 92, .	1.1	8
160	Bilayer avalanche spin-diode logic. AIP Advances, 2015, 5, 117102.	0.6	8
161	Excitons in CsPbBr ₃ Halide Perovskite. Journal of Physical Chemistry Letters, 2021, 12, 9301-9307.	2.1	8
162	Surface photovoltage spectroscopy of surface states on indium phosphide. Applied Physics Letters, 1988, 52, 1352-1354.	1.5	7

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163	BaTiO ₃ thin films for optically active waveguides. Integrated Ferroelectrics, 1995, 7, 25-31.	0.3	7
164	Metalorganic Molecular Beam Epitaxy of Magnesium Oxide on Silicon. Materials Research Society Symposia Proceedings, 2000, 619, 149.	0.1	7
165	Electronic structure of substitutional Mn in epitaxial In _{0.965} Mn _{0.035} Sb film. Applied Physics Letters, 2009, 95, 201905.	1.5	7
166	Transient photocurrent measurements in alkali chalcogenide ternary compound semiconductors. Semiconductor Science and Technology, 2013, 28, 015022.	1.0	7
167	Optical investigation of defects in semi-insulating $\text{Tl}_{1-x}\text{In}_x\text{Se}$ single crystals. Physical Review B, 2014, 90, .	1.1	7
168	Controlling the Vapor Transport Crystal Growth of Hg ₃ Se ₂ I ₂ Hard Radiation Detector Using Organic Polymer. Crystal Growth and Design, 2019, 19, 2074-2080.	1.4	7
169	The Chemical Vapor Deposition of Polycrystalline InP. Journal of the Electrochemical Society, 1980, 127, 2747-2750.	1.3	6
170	Compensation in Ge-doped InP. Journal of Applied Physics, 1990, 68, 606-609.	1.1	6
171	Rare-Earth Doped In _x Ga _{1-x} P Prepared by Metalorganic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 1991, 240, 195.	0.1	6
172	Solid phase epitaxy of Bi ₂ Sr ₂ CaCu ₂ O _x superconducting thin films. Journal of Applied Physics, 1993, 73, 4080-4082.	1.1	6
173	Effect of free carriers on the luminescence efficiency of InP:Er. Applied Physics Letters, 1994, 65, 845-847.	1.5	6
174	The Effects of Domain Structure on the Electro-Optic Response of Potassium Niobate Thin Films. Materials Research Society Symposia Proceedings, 1996, 453, 259.	0.1	6
175	Optical Study of GaN Doped with Mn Grown by Metal Organic Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2000, 639, 371.	0.1	6
176	Pressure dependence of the blue luminescence in Mg-doped GaN. Applied Physics Letters, 2000, 77, 2536-2538.	1.5	6
177	Nanosecond-Scale Domain Dynamics in BaTiO ₃ Probed by Time-Resolved X-Ray Diffraction. Ferroelectrics, 2003, 290, 115-124.	0.3	6
178	Integration of MgO on Si(001) Using SrO and SrTiO ₃ Buffer Layers by Molecular Beam Epitaxy. Journal of Electroceramics, 2004, 13, 149-154.	0.8	6
179	Photo-induced current transient spectroscopy of single crystal $\text{Tl}_6\text{I}_4\text{Se}$. Semiconductor Science and Technology, 2014, 29, 115002.	1.0	6
180	Charge Transport Mechanisms in a Pb ₂ P ₂ Se ₆ Semiconductor. ACS Photonics, 2016, 3, 1877-1887.	3.2	6

#	ARTICLE	IF	CITATIONS
181	Improved Crystal Growth of $\text{Tl}_{0.6}\text{Se}_{0.4}$ for β -Ray Detection Material by Oxide Impurity Removal. <i>Crystal Growth and Design</i> , 2017, 17, 6096-6104.	1.4	6
182	Defect levels in CsPbCl_3 single crystals determined by thermally stimulated current spectroscopy. <i>Journal of Applied Physics</i> , 2022, 132, .	1.1	6
183	Preparation of $\text{Ba}_{1-x}\text{Sr}_x\text{TiO}_3$ Thin Films by Metalorganic Chemical Vapor Deposition and Their Properties. <i>Materials Research Society Symposia Proceedings</i> , 1993, 335, 41.	0.1	5
184	Deep Level Defects in Mg-Doped GaN. <i>Materials Research Society Symposia Proceedings</i> , 1996, 423, 525.	0.1	5
185	Electrical Properties of Oxygen Doped GaN Grown by Metalorganic Vapor Phase Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1999, 595, 1.	0.1	5
186	Dynamic Response of the Electro-Optic Effect in Epitaxial Ferroelectric Thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1999, 597, 157.	0.1	5
187	Phase stability of heteroepitaxial polydomain BaTiO_3 thin films. <i>Journal of Materials Research</i> , 2007, 22, 1384-1389.	1.2	5
188	InMnAs magnetoresistive spin-diode logic. , 2012, , .		5
189	Photoluminescent properties of semiconducting $\text{Tl}_{0.6}\text{I}_{0.4}\text{Se}$. <i>Semiconductor Science and Technology</i> , 2012, 27, 015016.	1.0	5
190	Structural and magnetic properties of epitaxial $\text{In}_{1-x}\text{Mn}_x\text{Sb}$ semiconductor alloys with $x \leq 0.08$. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012, 30, 032801.	0.6	5
191	Charge Transport in Magnetic Semiconductor p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , 2015, 62, 2470-2474.	1.6	5
192	Function of cobalt and platinum on InP in the photoevolution of hydrogen from alkaline solutions. <i>Applied Physics Letters</i> , 1986, 49, 829-830.	1.5	4
193	Vapor phase epitaxy of InP using flow modulation. <i>Applied Physics Letters</i> , 1986, 49, 564-566.	1.5	4
194	Highly Strained $\text{InAs}_x\text{P}_{1-x}/\text{InP}$ Quantum wells Prepared by Flow Modulation Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1989, 145, 145.	0.1	4
195	Low Temperature Preparation of BaCuO High T_c Superconducting Thin Films by Plasma-Enhanced Organometallic Chemical Vapor Deposition. <i>Materials Research Society Symposia Proceedings</i> , 1989, 169, 593.	0.1	4
196	Organometallic Chemical Vapor Deposition of Strontium Titanate thin Films. <i>Materials Research Society Symposia Proceedings</i> , 1989, 168, 375.	0.1	4
197	Defect Luminescence in Heavily Mg Doped GaN. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1999, 4, 968-973.	1.0	4
198	Growth of MgO by Metal-Organic Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1999, 606, 45.	0.1	4

#	ARTICLE	IF	CITATIONS
217	Defect Structures in GaP/Si. Materials Research Society Symposia Proceedings, 1995, 399, 431.	0.1	2
218	Excitation Properties of Er-Doped GaP from Photoluminescence and High Pressure Studies. Materials Research Society Symposia Proceedings, 1996, 422, 279.	0.1	2
219	1.54 μm Electroluminescence from Erbium Doped Gallium Phosphide Diodes. Materials Research Society Symposia Proceedings, 1996, 422, 345.	0.1	2
220	The Optical Properties of Channel Waveguides in BaTiO ₃ Thin Films. Materials Research Society Symposia Proceedings, 1996, 446, 349.	0.1	2
221	Luminescence Efficiency of Erbium-Doped BaTiO ₃ Thin Films. Materials Research Society Symposia Proceedings, 1999, 597, 15.	0.1	2
222	Photoluminescence Studies of p-type GaN:Mg Co-doped with Oxygen. Materials Research Society Symposia Proceedings, 2000, 639, 6391.	0.1	2
223	Dielectric Properties of Spray Deposited BaTiO ₃ and Ba _{0.68} Sr _{0.32} TiO ₃ . Materials Research Society Symposia Proceedings, 2001, 698, 361.	0.1	2
224	Interfacial Layer Effects in Ba _{1-x} Sr _x TiO ₃ Thick Films prepared by Plasma Spray. Materials Research Society Symposia Proceedings, 2002, 758, 271.	0.1	2
225	Cyclotron resonance in InMnAs and InMnSb ferromagnetic films. Journal of Physics: Conference Series, 2011, 334, 012056.	0.3	2
226	Characterization of deep level defects in Ti ₆ Al ₄ S single crystals by photo-induced current transient spectroscopy. Journal Physics D: Applied Physics, 2015, 48, 075303.	1.3	2
227	Integrated BaTiO ₃ modulator with 8 dB extinction at 50 GHz and 25 km reach. , 2016, , .		2
228	Deep Level and Near-Band-Edge Recombination in Semiconducting Antiperovskite Hg ₃ Se ₂ I ₂ Single Crystals. Advanced Optical Materials, 2018, 6, 1800328.	3.6	2
229	Combinatorial Generation and Analysis of Nanometer- and Micrometer-Scale Silicon Features via Dip-Pen Nanolithography and Wet Chemical Etching. , 2000, 12, 1600.		2
230	Routes to High-T _c Superconducting TlBaCaCuO Films Using Organometallic Chemical Vapor Deposition. Materials Research Society Symposia Proceedings, 1989, 169, 623.	0.1	1
231	Heteroepitaxial Bi ₂ Sr ₂ CaCu ₂ O _x Superconducting thin films Deposited on LaAlO ₃ by Solid Phase Epitaxy and OMCVD. Materials Research Society Symposia Proceedings, 1992, 275, 443.	0.1	1
232	Ferroelectric Properties of a-Axis Textured BaTiO ₃ Thin Films. Materials Research Society Symposia Proceedings, 1993, 310, 319.	0.1	1
233	Defects and Electronic Transport in Rare Earth Doped Epitaxial SrTiO ₃ Thin Films. Materials Research Society Symposia Proceedings, 1996, 433, 21.	0.1	1
234	The Effects Of Substrate Thermal Mismatch on the Domain Structure of MOCVD-Derived Potassium Niobate Thin Films. Materials Research Society Symposia Proceedings, 1997, 474, 31.	0.1	1

#	ARTICLE	IF	CITATIONS
235	Epitaxial Ferroelectric Oxides for Electro-Optic and Non-Linear Optical Applications. Materials Research Society Symposia Proceedings, 1997, 495, 23.	0.1	1
236	Strain in Epitaxial BaTiO ₃ Thin Films Prepared by MOCVD. Materials Research Society Symposia Proceedings, 1998, 541, 489.	0.1	1
237	Epitaxial KNbO ₃ and its Nonlinear Optical Properties. Materials Research Society Symposia Proceedings, 1998, 541, 741.	0.1	1
238	Deep Donor-Acceptor Pair Luminescence in Codoped GaN. Materials Research Society Symposia Proceedings, 2002, 743, L5.8.1.	0.1	1
239	Measurement of Minority Carrier Diffusion Lengths in Semiconductor Nanowires. , 2006, , .		1
240	Ferroelectric Thin Film Microcavities and their Optical Resonant Properties. Materials Research Society Symposia Proceedings, 2009, 1182, 24.	0.1	1
241	High-performance computing based on spin-diode logic. Proceedings of SPIE, 2014, , .	0.8	1
242	Monte Carlo simulation of transport properties in wide gap Hg ₃ Se ₂ I ₂ . Semiconductor Science and Technology, 2019, 34, 115003.	1.0	1
243	Deposition of Strontium Barium Niobate Thin Films by Metal-Organic Chemical Vapor Deposition and Their Nonlinear Optical Properties. Materials Research Society Symposia Proceedings, 1994, 361, 167.	0.1	0
244	Enhanced Photoluminescence from Erbium-Doped Gap Microdisk Resonator. Materials Research Society Symposia Proceedings, 1995, 392, 229.	0.1	0
245	The Morphological Stability of Strained Epitaxial Layers. Materials Research Society Symposia Proceedings, 1996, 440, 335.	0.1	0
246	Defect Luminescence in Heavily Mg Doped GaN. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	0
247	Deep Level Formation in Undoped and Oxygen-Doped GaN. Materials Research Society Symposia Proceedings, 2000, 639, 11561.	0.1	0
248	Erbium-Doped Barium Titanate Thin Film Waveguides For Integrated Optical Amplifiers. Materials Research Society Symposia Proceedings, 2001, 694, 1.	0.1	0
249	InMnAs/InAs Heterojunctions for High-Field Magnetic Sensors. , 2006, , .		0
250	Bragg Reflector Waveguide and Electro-Optic Modulator Based on Barium Titanate Epitaxial Thin Films. Materials Research Society Symposia Proceedings, 2007, 1014, 1.	0.1	0
251	MAGNETORESISTANCE OF NARROW GAP MAGNETIC SEMICONDUCTOR HETEROJUNCTIONS. Spin, 2013, 03, 1340011.	0.6	0